The following Listing of Claims will replace all prior versions, and listings, of claims in the present application:

Listing of Claims:

1. (Currently amended) A method for making a dielectric structure for dual-damascene applications, the method comprising:

(a) providing a substrate;

(b) fabricating first metallization lines in the substrate;

(c) forming a barrier layer over the first metallization lines and the substrate; and

(d) forming an inter-metal dielectric structure, the forming of the inter-metal dielectric structure,

consisting the sequential steps of:

(d)(i) forming an inorganic dielectric layer to define a via dielectric layer directly over the barrier layer, the inorganic dielectric layer being highly selective relative to the barrier layer when etched;

(d)(ii) forming a carbon doped oxide layer to define a trench dielectric layer that is defined directly over and in direct contact with the inorganic dielectric layer, the trench layer being formed to define a metallization line layer of the inter-metal dielectric structure;

(d)(iii) forming a trench in the carbon doped oxide layer using a first etch chemistry to etch the carbon doped oxide layer; and

(d)(iv) forming a via in the inorganic dielectric layer from within the trench using a second etch chemistry to etch the inorganic dielectric layer, the second etch chemistry being different than the first etch chemistry.

2. Canceled.

3. Canceled.

4. (Original) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the barrier layer is one of a silicon nitride layer and a silicon carbide layer.

5. (Previously Presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer is a TEOS silicon dioxide material.

6. (Previously presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the carbon doped oxide layer is a low dielectric constant layer having a dielectric constant of about and no greater than 3.0.

7. (Previously Presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer is one of a TEOS oxide layer and a fluorine doped oxide layer.

8. (Previously presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 7, wherein the first etch chemistry is

optimized to etch through the carbon doped oxide layer and the second etch chemistry is optimized to etch through one of the TEOS oxide layer and the fluorine doped oxide layer.

9. (Original) A method for making a dielectric structure for dual-damascene applications as recited in claim 8, wherein the second etch chemistry is selective to the barrier layer.

10.-32. Canceled.

33. (Previously presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer has a thickness between about 0.4 microns (μ) and 0.5 microns

34. (Previously presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the carbon doped oxide layer has a thickness between about 0.5 microns and 0.6 microns.

35. (Previously presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer has a dielectric constant of about 4.